



| | | |
|--|-----------------------------|-----------------------------|
| FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICATION | ATTY. DOCKET NO.:9003-US-PA | APPLICATION NO.: 10/709,008 |
| | APPLICANT: Chang | |
| | FILING DATE: April 7, 2004 | GROUP 2812 |

U.S. PATENT DOUCMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FIILNG DATE (IF APPROPRIATE) |
|---------------------|--------------------|------------|--------------|----------------|----------------|------------------------------------|
| S.B.G. | 2002/0115245 | 2002/08/22 | Chang et al. | 438 | 166 | 2001/02/21 |
| / | | | | | | |
| | | | | | | |

FOREIGN PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | FIILNG DATE (IF APPROPRIATE) |
|---------------------|-----------------|------|---------|-------|----------|---------------------------------|
| / | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |

| EXAMINER INITIAL | OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) |
|---------------------|---|
| S.B.G. | Brotherton et al., Excimer-Laser-Annealed Poly-Si Thin-Film Transistors in <i>IEEE Transactions On Electron Devices</i> , Vol. 40, No. 2, pp. 407-413, February 1993. |
| S.B.G. | Zeng et al. , A Novel Two-Step Laser Crystallization Technique for Low- Temperature Poly-Si TFTs in <i>IEEE Transactions On Electron Devices</i> , Vol. 48, No. 5, pp. 1008-1010, May 2001. |
| / | |

| | |
|------------------------|-------------------------------|
| EXAMINER <u>S.B.G.</u> | DATE CONSIDERED <u>2-1-05</u> |
|------------------------|-------------------------------|

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.